

1. DESCRIPTION

The XD4069 is a general purpose hex unbuffered inverter. Each inverter has a single stage.

It operates over a recommended VDD power supply range of 3 V to 15 V referenced to VSS (usually ground). Unused inputs must be connected to VDD, VSS, or another input.

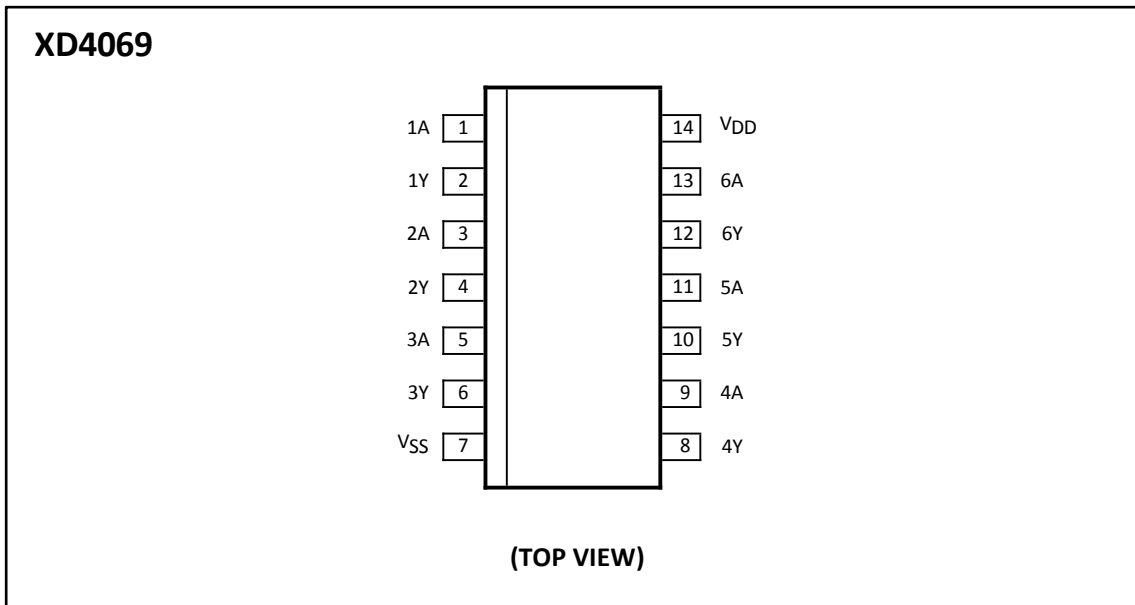
2. FEATURES

- Fully static operation
- 5 V, 10 V, and 15 V parametric ratings
- Standardized symmetrical output characteristics
- Specified from -25°C to +85°C
- Complies with JEDEC standard JESD 13-B

3. APPLICATIONS

- Logic inversion
- Pulse shaping
- Oscillators
- High-input-impedance amplifiers

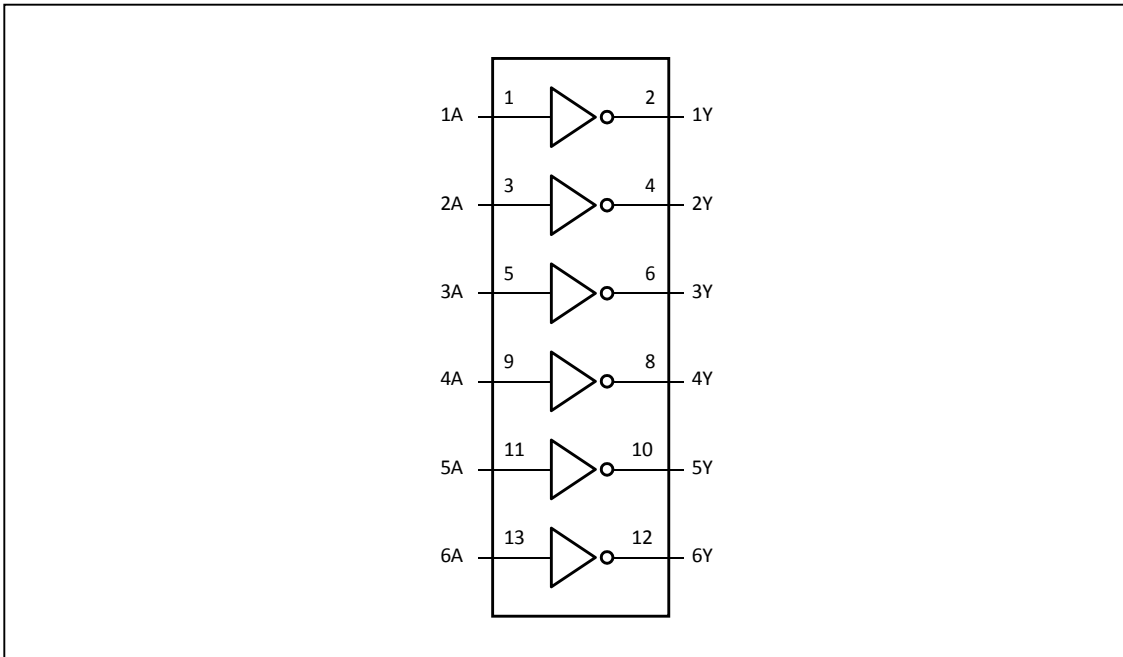
4. PIN CONFIGURATIONS AND FUNCTIONS



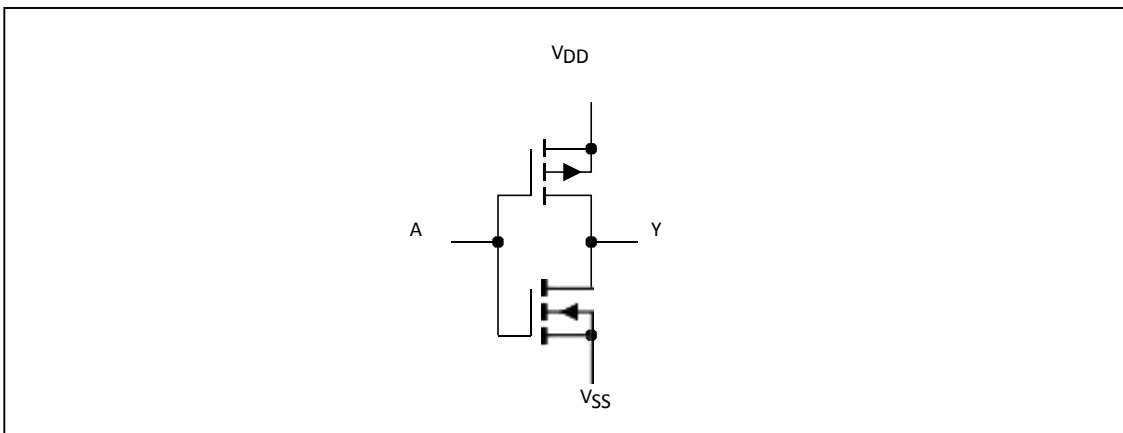
Pin Functions

Symbol	PIN	Description
1A to 6A	1, 3, 5, 9, 11, 13	input
1Y to 6Y	2, 4, 6, 8, 10, 12	output
VSS	7	ground (0 V)
VDD	14	supply voltage

5. FUNCTIONAL BLOCK DIAGRAM



Block Diagram



Schematic diagram (one inverter)

6. SPECIFICATIONS

6.1. Limiting values

In accordance with the Absolute Maximum Rating System .

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DD}	supply voltage		-0.5	+18	V
I_{IK}	input clamping current	$V_I < -0.5\text{ V}$ or $V_I > V_{DD} + 0.5\text{ V}$	-	± 10	mA
V_I	input voltage		-0.5	$V_{DD} + 0.5$	V
I_{OK}	output clamping current	$V_O < -0.5\text{ V}$ or $V_O > V_{DD} + 0.5\text{ V}$	-	± 10	mA
$I_{I/O}$	input/output current		-	± 10	mA
I_{DD}	supply current		-	50	mA
T_{stg}	storage temperature		-50	+150	°C
T_{amb}	ambient temperature		-25	+85	°C
P_{tot}	total power dissipation	$T_{amb} = -25\text{ °C to }+85\text{ °C}$			
		DIP14 (XD4069) ^[1]	-	500	mW
P	power dissipation	per output	-	100	mW

[1] For DIP14 packages: above $T_{amb} = 70\text{ °C}$, P_{tot} derates linearly with 8 mW/K.

6.2. Recommended Operating Conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DD}	supply voltage		3	-	15	V
V_I	input voltage		0	-	V_{DD}	V
T_{amb}	ambient temperature	in free air	-25	-	+85	°C

6.3. Static Characteristics

VSS = 0 V; VI = VSS or VDD; unless otherwise specified.

Symbol	Parameter	Conditions	VDD	T _{amb} = -25 °C		T _{amb} = +25 °C		T _{amb} = +85 °C		Unit
				Min	Max	Min	Max	Min	Max	
V _{IH}	HIGH-level input voltage	I _o < 1 μA	5 V	4	-	4	-	4	-	V
			10 V	8	-	8	-	8	-	V
			15 V	12.5	-	12.5	-	12.5	-	V
V _{IL}	LOW-level input voltage	I _o < 1 μA	5 V	-	1	-	1	-	1	V
			10 V	-	2	-	2	-	2	V
			15 V	-	2.5	-	2.5	-	2.5	V
V _{OH}	HIGH-level output voltage	I _o < 1 μA	5 V	4.95	-	4.95	-	4.95	-	V
			10 V	9.95	-	9.95	-	9.95	-	V
			15 V	14.95	-	14.95	-	14.95	-	V
V _{OL}	LOW-level output voltage	I _o < 1 μA	5 V	-	0.05	-	0.05	-	0.05	V
			10 V	-	0.05	-	0.05	-	0.05	V
			15 V	-	0.05	-	0.05	-	0.05	V
I _{OH}	HIGH-level output current	V _o = 2.5 V	5 V	-	-1.7	-	-1.4	-	-1.1	mA
		V _o = 4.6 V	5 V	-	-0.64	-	-0.5	-	-0.36	mA
		V _o = 9.5 V	10 V	-	-1.6	-	-1.3	-	-0.9	mA
		V _o = 13.5 V	15 V	-	-4.2	-	-3.4	-	-2.4	mA
I _{OL}	LOW-level output current	V _o = 0.4 V	5 V	0.64	-	0.5	-	0.36	-	mA
		V _o = 0.5 V	10 V	1.6	-	1.3	-	0.9	-	mA
		V _o = 1.5 V	15 V	4.2	-	3.4	-	2.4	-	mA
I _i	input leakage current		15 V	-	±0.1	-	±0.1	-	±1.0	μA
I _{DD}	supply current	all valid input combinations; I _o = 0 A	5 V	-	0.6	-	0.4	-	10	μA
			10 V	-	1.0	-	1.2	-	18	μA
			15 V	-	1.8	-	2.5	-	35	μA
C _i	input capacitance	digital inputs		-	-	-	7.5	-	-	pF

6.4. Dynamic Characteristics

Tamb = 25 °C; for waveforms see Figure 7-1; for test circuit see Figure 7-2.

Symbol	Parameter	Conditions	VDD	Extrapolation formula ^[1]	Min	Typ	Max	Unit
t _{PHL}	HIGH to LOW propagation delay	nA to nY;	5 V	18 ns + (0.55 ns/pF)C _L	-	45	90	ns
			10 V	9 ns + (0.23 ns/pF)C _L	-	20	40	ns
			15 V	7 ns + (0.16 ns/pF)C _L	-	15	25	ns
t _{PLH}	LOW to HIGH propagation delay	nA to nY	5 V	13 ns + (0.55 ns/pF)C _L	-	40	80	ns
			10 V	9 ns + (0.23 ns/pF)C _L	-	20	40	ns
			15 V	7 ns + (0.16 ns/pF)C _L	-	15	30	ns
t _{THL}	HIGH to LOW output transition time	output nY	5 V	10 ns + (1.00 ns/pF)C _L	-	60	120	ns
			10 V	9 ns + (0.42 ns/pF)C _L	-	30	60	ns
			15 V	6 ns + (0.28 ns/pF)C _L	-	20	40	ns
t _{TLH}	LOW to HIGH output transition time	output nY	5 V	10 ns + (1.00 ns/pF)C _L	-	60	120	ns
			10 V	9 ns + (0.42 ns/pF)C _L	-	30	60	ns
			15 V	6 ns + (0.28 ns/pF)C _L	-	20	40	ns

[1] The typical value of the propagation delay and output transition time can be calculated with the extrapolation formula (C_L in pF).

6.5. Dynamic power dissipation

VSS = 0 V; tr = tf ≤ 20 ns; Tamb = 25 °C.

Symbol	Parameter	VDD	Typical formula	Where
P _D	dynamic power dissipation	5 V	$P_D = 600 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$ (μW)	f _i = input frequency in MHz; f _o = output frequency in MHz; C _L = output load capacitance in pF; Σ(f _o × C _L) = sum of the outputs; V _{DD} = supply voltage in V.
		10 V	$P_D = 4000 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$ (μW)	
		15 V	$P_D = 22000 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$ (μW)	

7. WAVEFORMS

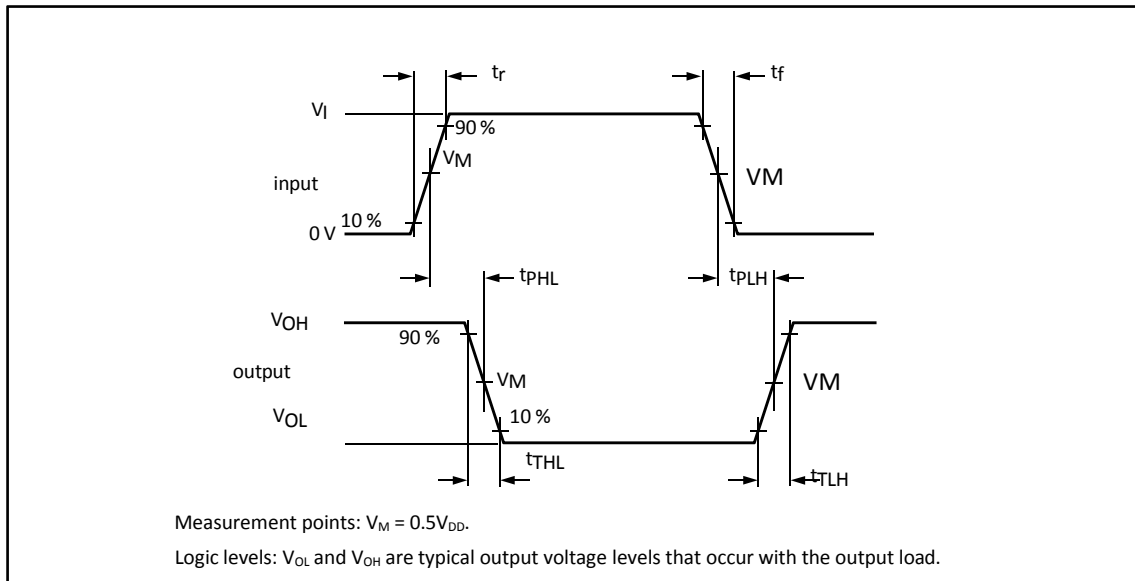


Fig 7-1. Propagation delay and transition times

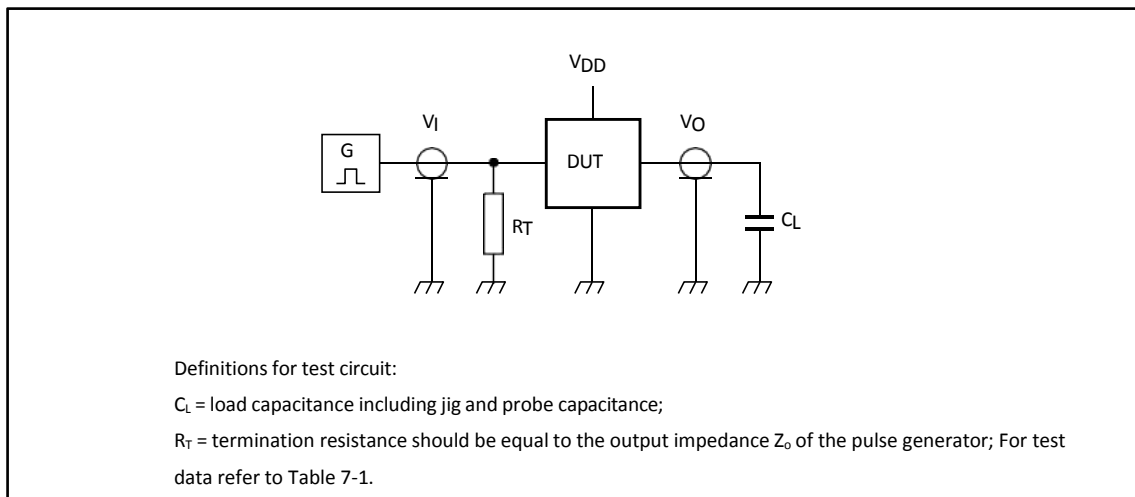


Fig 7-2. Test circuit for measuring switching times

Table7-1. Test data

Supply voltage	Input		Load
V_{DD}	V_I	t_r, t_f	C_L
5 V to 15 V	V_{SS} or V_{DD}	≤ 20 ns	50 pF

7.1. Transfer characteristics

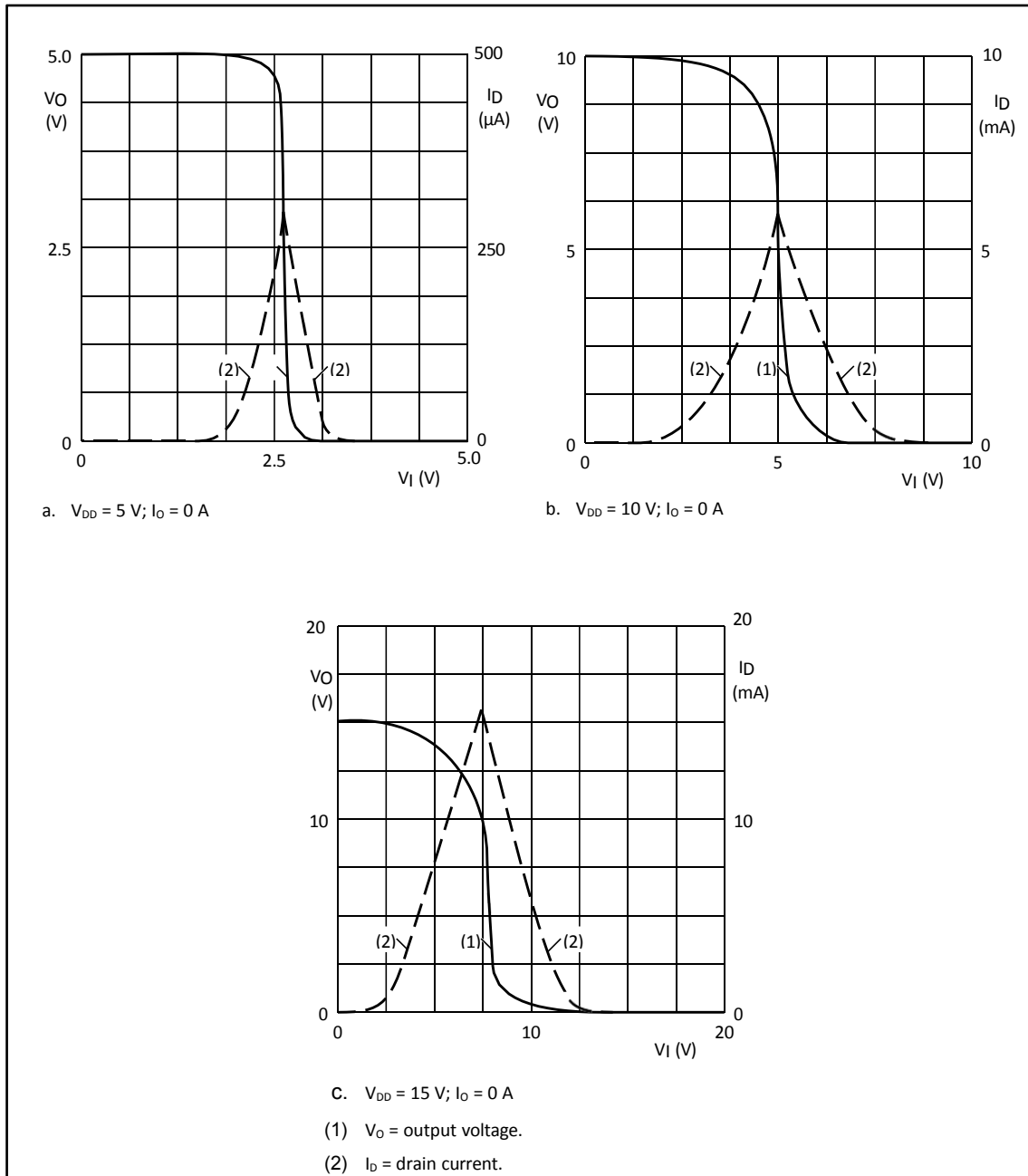


Fig 7-3. Typical transfer characteristics

8. Application information

Some examples of applications for the XD4069.

Figure 8-1 shows an astable relaxation oscillator using two XD4069 inverters and 2 BAW62 diodes. The oscillation frequency is mainly determined by $R1 \times C1$, provided $R1 \ll R2$ and $R2 \times C2 \ll R1 C1$.

The function of $R2$ is to minimize the influence of the forward voltage across the protection diodes on the frequency; $C2$ is a stray (parasitic) capacitance.

The period T_p is given by $T_p = T_1 + T_2$, where:

$$T_1 = R1C1 \ln \frac{V_{DD} + V_{ST}}{V_{ST}}$$

$$T_2 = R1C1 \ln \frac{2V_{DD} - V_{ST}}{V_{DD} - V_{ST}}$$

V_{ST} = the signal threshold level of the inverter.

The period is fairly independent of V_{DD} , V_{ST} and temperature. The duty factor, however, is influenced by V_{ST} .

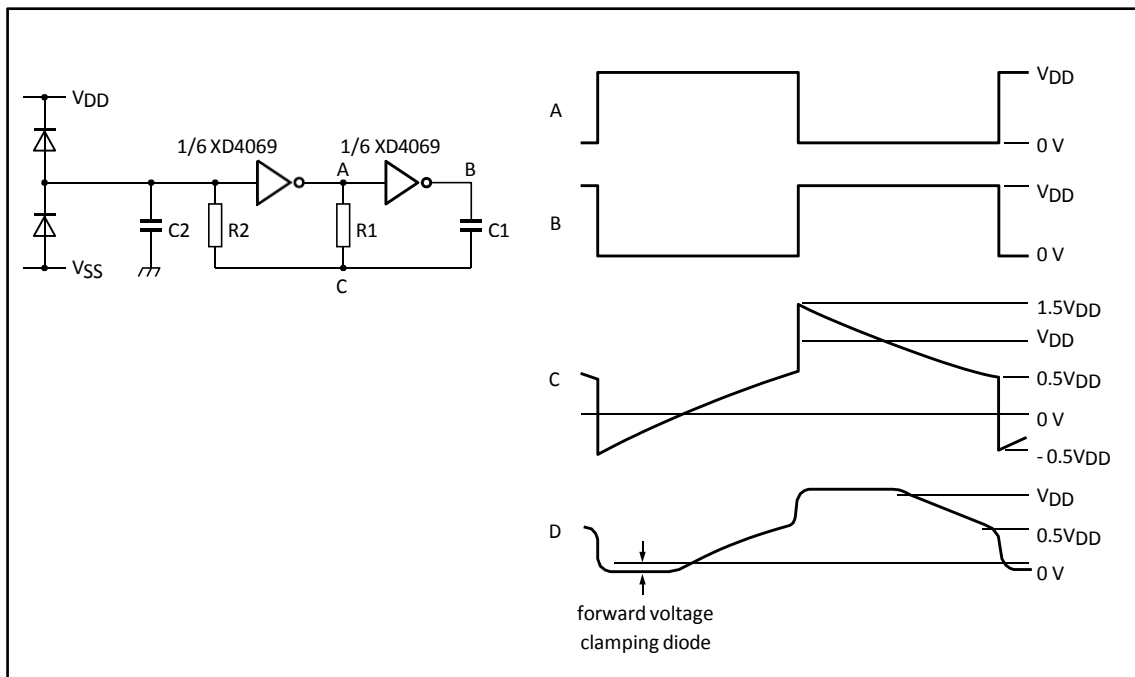


Fig 8-1. Astable relaxation oscillator

Figure 8-2 shows a crystal oscillator for frequencies up to 10 MHz using two XD4069 inverters. The second inverter amplifies the oscillator output voltage to a level sufficient to drive other Local Oxidation CMOS (LOCMOS) circuits.

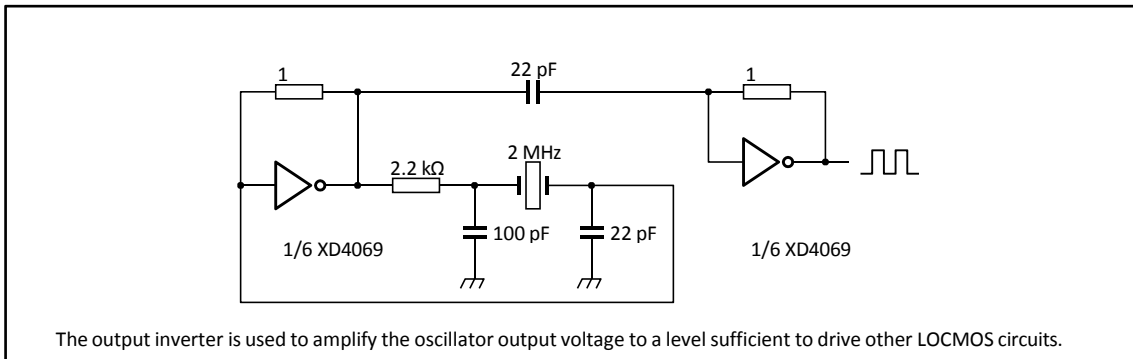


Fig 8-2. Crystal oscillator

Figure 8-3 and Figure 8-4 show voltage gain and supply current. Figure 11 shows the test set-up and an example of an analog amplifier using one XD4069.

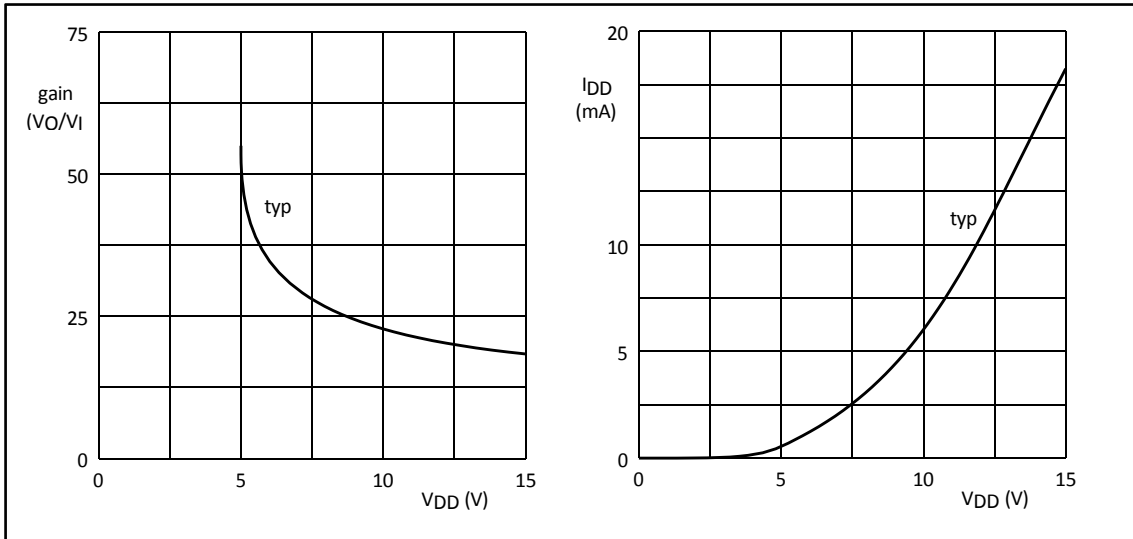


Fig 8-3. Typical voltage gain as a function of supply voltage

Fig 8-4. Typical supply current as a function of supply voltage

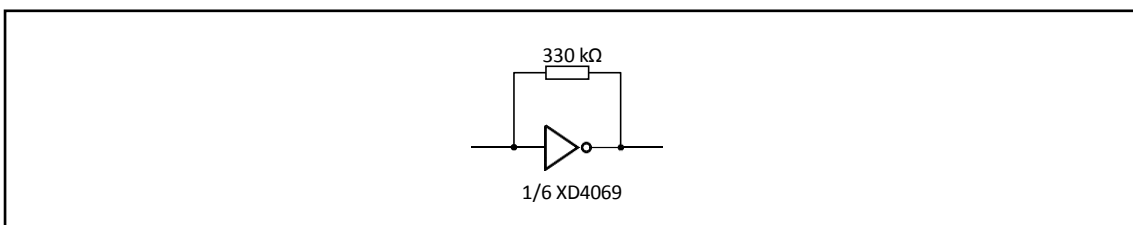


Fig 8-5. Test set-up

Figure 8-6 shows typical forward transconductance and Figure 8-7 shows the test set-up.

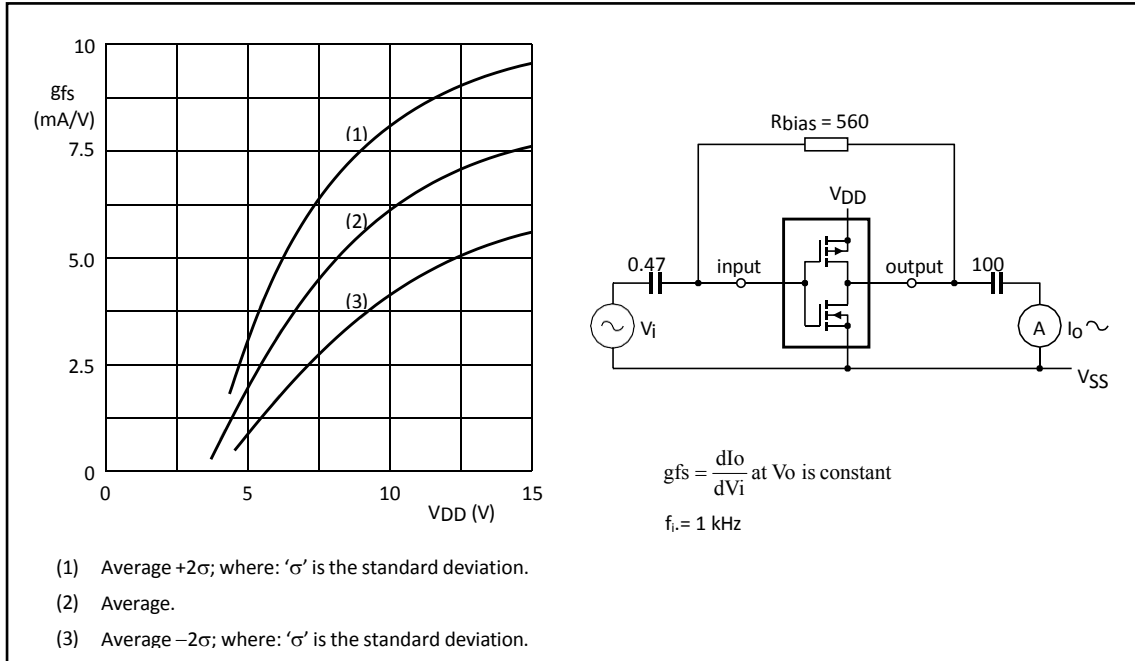
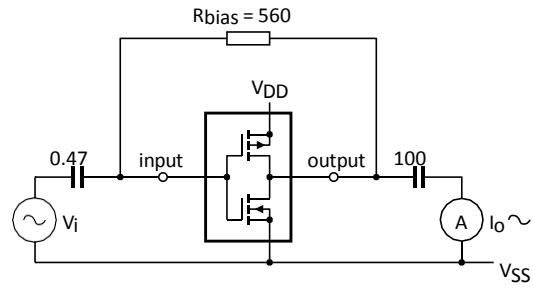


Fig 8-6. Typical forward transconductance as a function of supply voltage at Tamb = 25 °C



$$g_{fs} = \frac{dI_o}{dV_i} \text{ at } V_o \text{ is constant}$$

$$f_i = 1 \text{ kHz}$$

Fig 8-7. Test set-up

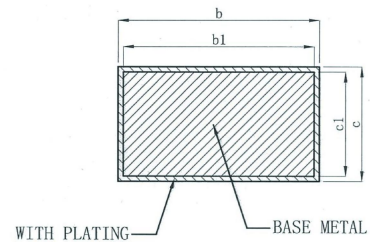
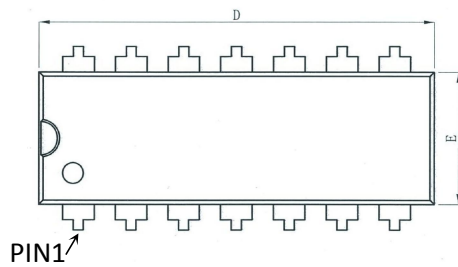
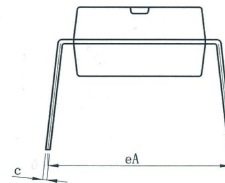
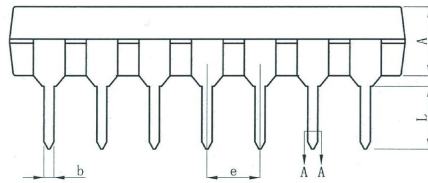
9. ORDERING INFORMATION

Ordering Information

Part Number	Device Marking	Package Type	Body size (mm)	Temperature (°C)	MSL	Transport Media	Package Quantity
XD4069	XD4069	DIP14	19.05 * 6.35	-25 to +85	MSL3	Tube 25	1000

10. DIMENSIONAL DRAWINGS

DIP14



SECTION A-A

symbol	millimeter		
	Min	Nom	Max
A	3.20	3.30	3.40
b	0.44	---	0.53
b1	0.43	0.46	0.49
c	0.25	---	0.30
c1	0.24	0.25	0.26
D	18.95	19.05	19.15
E	6.25	6.35	6.45
e	2.54BSC		
eA	8.30	8.80	9.30
L	3.00	---	---